

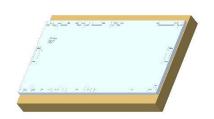
27.5 - 31 GHz GaN 34 W Power Amplifier

Product Description

The Nxbeam NPA2003-TB-501 is a Ka-band high power amplifier MMIC fabricated in 0.2um GaN HEMT on SiC mounted on a high thermal conductive heat spreader (tab). The MMIC operates from 27.5 to 31 GHz and provides an average of 34 W saturated output power, 31% PAE, and 25 dB of linear gain. The NPA2003-TB-501 comes in die-on-tab form with RF input and output matched to 50 Ω with DC blocking capacitors for easy system integration. The HEMT devices are fully passivated for reliable operation. Bond pad and backside metallization are Au-based for compatibility with eutectic die attachment methods.

Applications

- Ka-band Satellite Communications
- 5G Infrastructure
- Point-to-Point/Multipoint Digital Radios



Key Features

Frequency: 27.5 – 31 GHzLinear Gain (Ave.): 25 dBPsat (Ave.): 34 W

• PAE (Ave.): 31%

Electrical Specifications

Test Condition: Vd = 24 V, Idq = 2.0 A, CW Performance in Fixture, Typical Performance at 25°C

Parameter		Min	Typical	Max	Unit
Frequency		27.5		31	GHz
	27.5 GHz		25		
Gain (Small Signal)	29 GHz	23	25.3	27	dB
	31 GHz		25		
	27.5 GHz		45.4		
Output Power (at Psat, Pin=26 dBm)	29 GHz	44	45.1		dBm
	31 GHz		45		
	27.5 GHz		32.1		
PAE (at Psat, Pin=26 dBm)	29 GHz		32.0		%
	31 GHz		30.2		
	27.5 GHz		19.6		
Power Gain (at Psat, Pin=26 dBm)	29 GHz		20.9		dB
	31 GHz		20.3		
	27.5 GHz		20		
Input Return Loss	29 GHz		20		dB
	31 GHz		11		
	27.5 GHz		8		
Output Return Loss	29 GHz		13		dB
	31 GHz		8		

Maximum Quiescent Bias

Parameter	Max	Unit
Drain Voltage (Vd1, Vd2, Vd3)	28	٧
Drain Current (Id1)	264	mA
Drain Current (Id2)	640	mA
Drain Current (Id3)	2112	mA

Maximum quiescent bias represents the operational bias used during reliability life testing. Biasing the part at or below this bias ensures reliability will be bound by the published reliability results.

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Absolute Maximum Ratings (Temp. = 25°C)

Parameter	Min	Max	Unit
Drain Voltage (Vd1, Vd2, Vd3)		28	٧
Drain Current (Id1)		660	mA
Drain Current (Id2)		1600	mA
Drain Current (Id3)		5250	mA
Gate Voltage (Vg1, Vg2, Vg3)	-8	0	V

Absolute maximum ratings represent the maximum current under power saturation conditions.

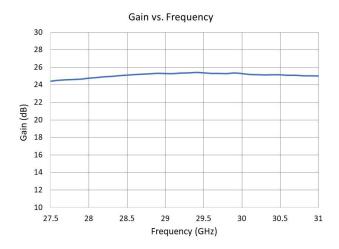
Recommended Quiescent Operating Condition

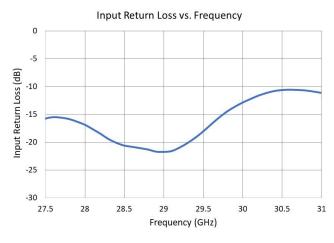
Parameter	Value	Unit
Drain Voltage (Vd)	20 - 28	V
Drain Current (Id1)	up to 264	mA
Drain Current (Id2)	up to 640	mA
Drain Current (Id3)	up to 2112	mA
Gate Voltage (Vg) (Typical Range)	-4	V

Gate voltage will vary based on desired current per stage

Small Signal Performance

Test Condition: Vd = 24 V, Idq = 2.0 A, (CW Performance in Fixture, Typical Performance at 25°C)







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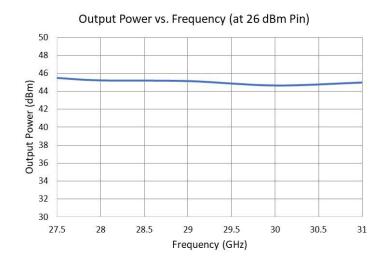


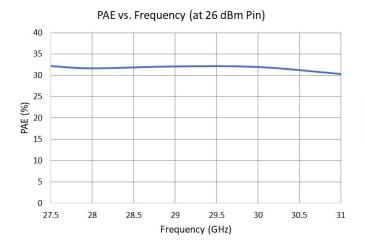


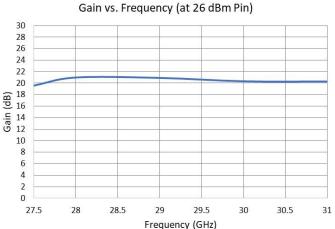
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Large Signal Performance

Test Condition: Vd = 24 V, Idq = 2.0 A, Pin = 26 dBm (Psat) (CW Performance in Fixture, Typical Performance at 25°C)







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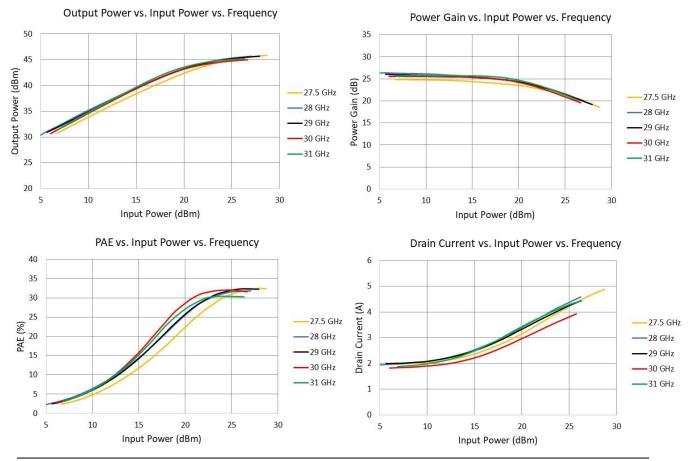
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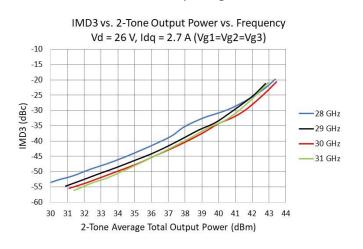
Large Signal Performance

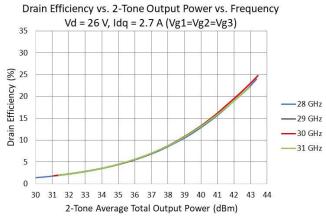
Test Condition: Vd = 24 V, Idq = 2.0 A, (CW Performance in Fixture, Typical Performance at 25°C)



2-Tone Linearity Performance

10 MHz Tone Spacing, CW Performance in Fixture, Typical Performance at 25°C,





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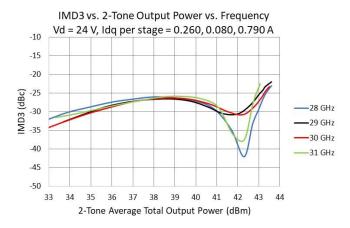


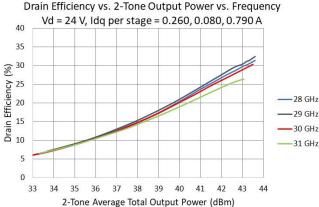


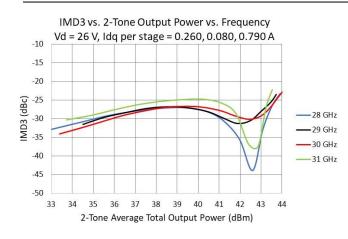
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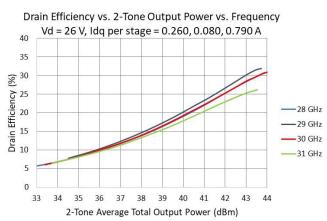
2-Tone Linearity Performance

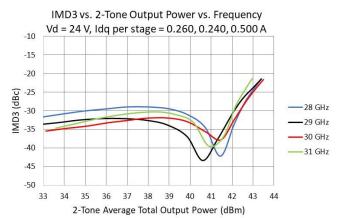
10 MHz Tone Spacing, CW Performance in Fixture, Typical Performance at 25°C, Gate Voltages Biased Separately

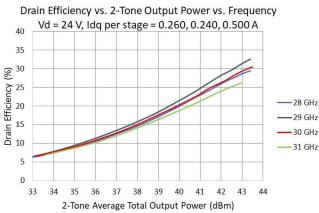












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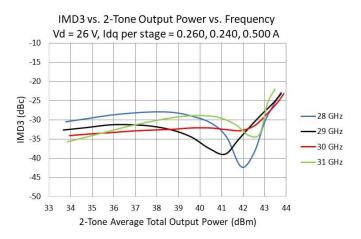


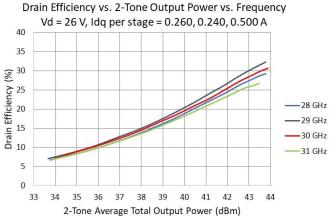


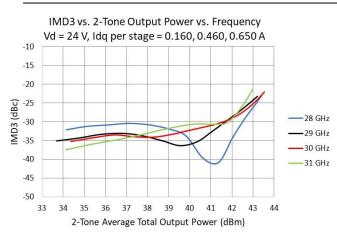
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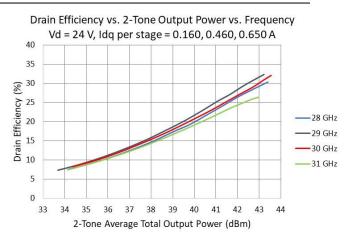
2-Tone Linearity Performance

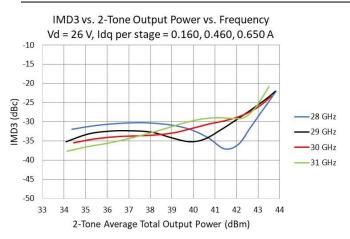
10 MHz Tone Spacing, CW Performance in Fixture, Typical Performance at 25°C, Gate Voltages Biased Separately

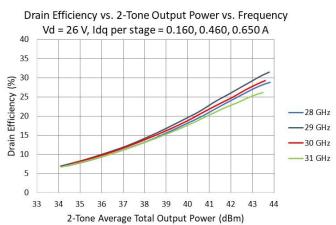












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Thermal Information

RF = Off

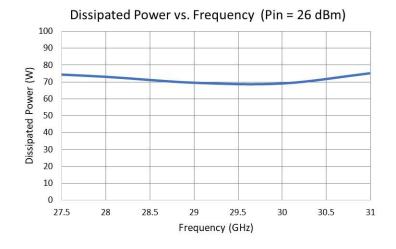
Parameter	Condition	Value	Unit
Thermal Resistance (R _{OJC})	RF=OFF	1.41	°C/W
Junction Temperature (Tj)	T _{backside} =85 °C, V _d =24 V, I _{dq} =2.0 A, P _{dis} =48 W	152.6	°C

RF = On, Peak Junction Temperature at Pin = 26 dBm (Psat), CW Performance in Fixture

Parameter	Condition	Value	Unit
Thermal Resistance (R _{OJC})	P _{in} =26 dBm, Freq.=31 GHz	1.54	°C/W
Junction Temperature (Tj)	T _{backside} =85 °C, V _d =24 V _, I _d =4.57 A _, P _{dis} =75.3 W	200.9	°C

Note 1: Thermal resistance determined to the back of the tab.

Note 2: Mean time to failure per junction temperature information can be found in the following document: Nxbeam_GaN20MMIC_Reliability.pdf



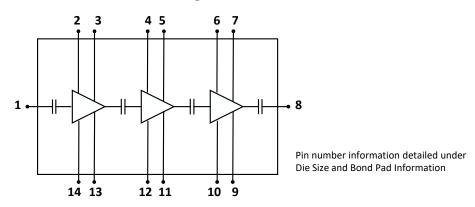
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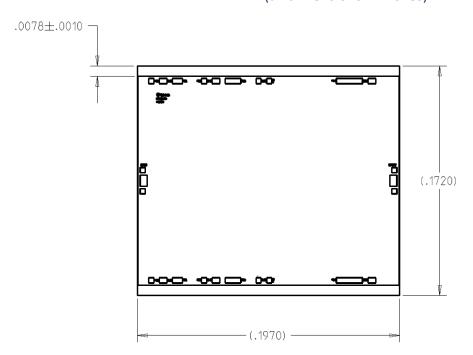


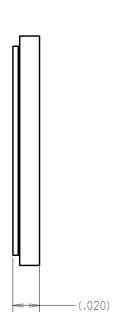
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Circuit Block Diagram



Product Dimensions (all dimensions in inches)





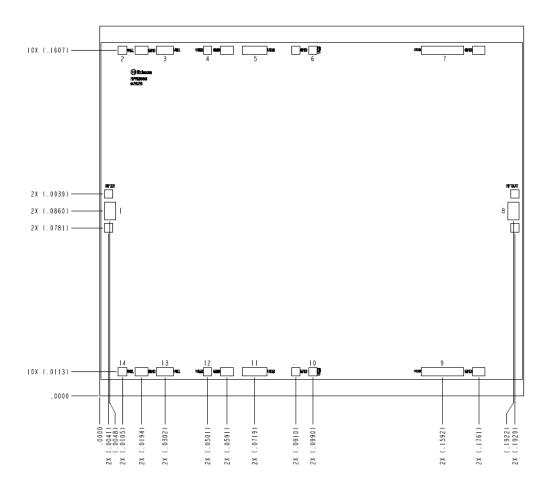
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Die Size and Bond Pad Information

	TABLE I: INTERFACE IDEN	NTIFICATION	l
I D	FUNCTION	PAD NUMBER	PAD SIZE (MICRONS)
RFIN	RF INPUT	1	134 X 208
RFOUT	RF OUTPUT	8	134 X 208
VGI	GATE VOLTAGE - STAGE I (-8V MIN, OV MAX)	2,14	100 X 100
VDI	DRAIN VOLTAGE – STAGE I (OV MIN, 28V MAX)	3,13	196 X 100
VG2	GATE VOLTAGE - STAGE 2 (-8V MIN, OV MAX)	4,12	100 X 100
VD2	DRAIN VOLTAGE - STAGE 2 (OV MIN, 28V MAX)	5,11	296 X 100
VG3	GATE VOLTAGE - STAGE 3 (-8V MIN, OV MAX)	6,10	96 X 100
VD3	DRAIN VOLTAGE - STAGE 3 (OV MIN, 28V MAX)	7,9	500 X 100



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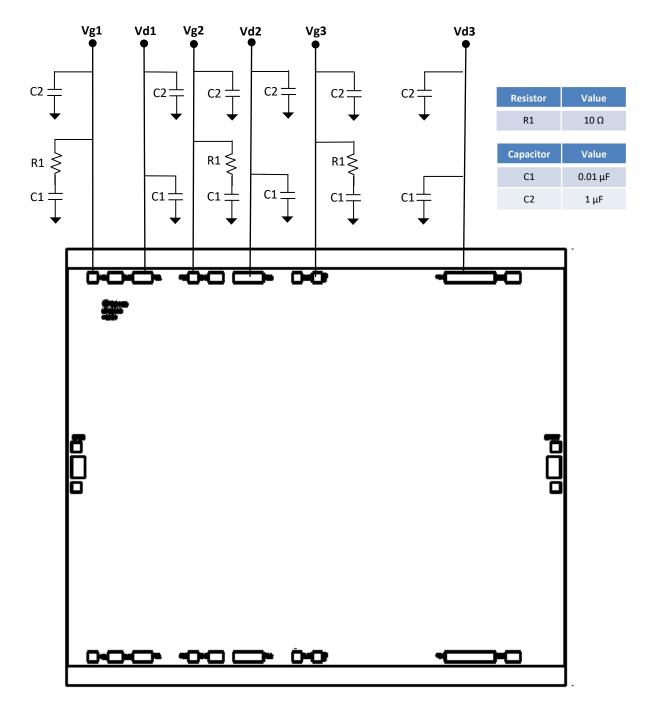




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Suggested Off-Chip Components

The following diagram is a suggested bonding arraignment with off-chip components. All drain connections can be tied together to one source. All gate connections can be tied together to one source if desired. The NPA2003-TB-501 should be biased for both sides of the chip.



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Assembly Process

- The heat spreader is gold plated and can be mounted using either a high thermal conductive epoxy or solder attachment.
- Maximum recommended temperature during product attachment is 260 °C for not more than 60 seconds.
- This product contains metal air bridges so caution should be taken when handling to avoid damage.

Bias Information

Bias-up Procedure:

- 1.) It is recommended that voltage and current limits are set on the voltage supply's prior to biasing the product.
- 2.) Ensure power supplies are properly grounded to the product test fixture.
- 3.) Apply a negative gate voltage of -7V to Vg1, Vg2, and Vg3 to ensure all devices are pinched off.
- 4.) Gradually increase the drain bias voltage (Vd1, Vd2, Vd3) to the desired bias level but not to exceed the maximum voltage of 28 V.
- 5.) Gradually increase the gate voltages (Vg1, Vg2, Vg3) while monitoring the drain current until the desired drain current in each stage is achieved.
- 6.) Apply RF signal.

Bias-down Procedure:

- 1.) Turn off RF signal.
- 2.) Gradually decrease Vg1, Vg2, and Vg3 down to -7 V.
- 3.) Gradually decrease the drain voltages (Vd1, Vd2, Vd3) down to 0 V.
- 4.) Gradually increase gate voltages (Vg1, Vg2, Vg3) to 0 V.
- 5.) Turn off supply voltages

ESD Sensitive Product



Important Information

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